SIEMENS

3.3V 4M x 64/72-Bit 1 BANK SDRAM Module HYS64(72)V4200GU
3.3V 8M x 64/72-Bit 2 BANK SDRAM Module HYS64(72)V8220GU

PC66 & PC100 168 pin unbuffered DIMM Modules

- 168 Pin unbuffered 8 Byte Dual-In-Line SDRAM Modules for PC main memory applications
- One bank 4M x 64, 4Mx72 and two bank 8M x 64, 8M x 72 organisation
- Optimized for byte-write non-parity and ECC applications
- JEDEC standard Synchronous DRAMs (SDRAM)
- Fully PC board layout compatible to INTEL's Rev. 1.0 module specification
- SDRAM Performance:

		-8	-8B	-10	Units
f_{CK}	Clock frequency (max.)	100	100	66	MHz
t_{AC}	Clock access time	6	6	8	ns

- Programmed Latencies :

Product Speed		CL	tRCD	tRP
-8	PC100	2	2	2
-8B	PC100	3	2	3
-10	PC66	2	2	2

- Single +3.3V(± 0.3V) power supply
- Programmable $\overline{\text{CAS}}$ Latency, Burst Length and Wrap Sequence (Sequential & Interleave)
- Auto Refresh (CBR) and Self Refresh
- Decoupling capacitors mounted on substrate
- All inputs, outputs are LVTTL compatible
- Serial Presence Detect with E^2PROM
- Utilizes 4M x16 SDRAMs in TSOPII-54 packages
- 4096 refresh cycles every 64 ms
- 133,35 mm x 29,31 mm x 4,00 mm card size with gold contact pads

The HYS64(72)V4200 and HYB64(72)V8220 are an industry standard 168-pin 8-byte Dual in-line Memory Module (DIMM) which are organised as 4M x 64, 4M x 72 in an one bank and 8M x 64, 8M x72 in two banks high speed memory arrays designed with 64Mbit Synchronous DRAMs (SDRAMs Die Rev.B) for non-parity and ECC application. The DIMMs use -8 and -8B speed sort 4M x 16 SDRAM devices in TSOP54 packages to meet the PC100 requirements and -10 parts for 66 MHz bus speed applications. Decoupling capacitors are mounted on the PC board. The PC board design is according to INTEL's module specification.

The DIMMs have a serial presence detect, implemented with a serial E^2PROM using the two pin I^2C protocol. The first 128 bytes are utilized by the DIMM manufacturer and the second 128 bytes are available to the end user.

All SIEMENS 168-pin DIMMs provide a high performance, flexible 8-byte interface in a 133,35 mm long footprint, with t.d.b. height.

Ordering Information

Type	Ordering Code	Package	Descriptions	Module Height
HYS 64V4200GU-8	PC100-222-620	L-DIM-168-31	100 Mhz 4M x 64 1 bank SDRAM module	1,15"
HYS 72V4200GU-8	PC100-222-620	L-DIM-168-31	100 MHz 4M x 72 1 bank SDRAM module	1,15"
HYS 64V8220GU-8	PC100-222-620	L-DIM-168-31	100 Mhz 8M x 64 2 bank SDRAM module	1,15"
HYS 64V8220GU-8	PC100-222-620	L-DIM-168-31	100 MHz 8M x 72 2 bank SDRAM module	1,15"
HYS 64V4200GU-8B	PC100-323-620	L-DIM-168-31	100 Mhz 4M x 64 1 bank SDRAM module	1,15"
HYS 64V8220GU-8B	PC100-323-620	L-DIM-168-31	100 Mhz 8M x 64 2 bank SDRAM module	1,15"
HYS 64V4200GU-10	PC66-222-620	L-DIM-168-31	66 Mhz 4M x 64 1 bank SDRAM module	1,15"
HYS 72V4200GU-10	PC66-222-620	L-DIM-168-31	66 MHz 4M x 72 1 bank SDRAM module	1,15"
HYS 64V8220GU-10	PC66-222-620	L-DIM-168-31	66 Mhz 8M x 64 2 bank SDRAM module	1,15"
HYS 64V8220GU-10	PC66-222-620	L-DIM-168-31	66 MHz 8M x 72 2 bank SDRAM module	1,15"

Pin Names

A0-A11	Address Inputs (RA0~ RA11 / CA0 ~ CA7, CA10)	CLK0 - CLK3	Clock Input
BA0 , BA1	Bank Select	DQMB0 - DQMB7	Data Mask
DQ0 - DQ63	Data Input/Output	$\overline{CS0}$ - $\overline{CS3}$	Chip Select
CB0-CB7	Check Bits (x 72 organisation only)	Vcc	Power (+3.3 Volt)
$\overline{RAS}$	Row Address Strobe	Vss	Ground
$\overline{CAS}$	Column Address Strobe	SCL	Clock for Presence Detect
$\overline{WE}$	Read / Write Input	SDA	Serial Data Out for Pres. Detect
$\overline{CKE0}$, $\overline{CKE1}$	Clock Enable	N.C. / DU	No Connection

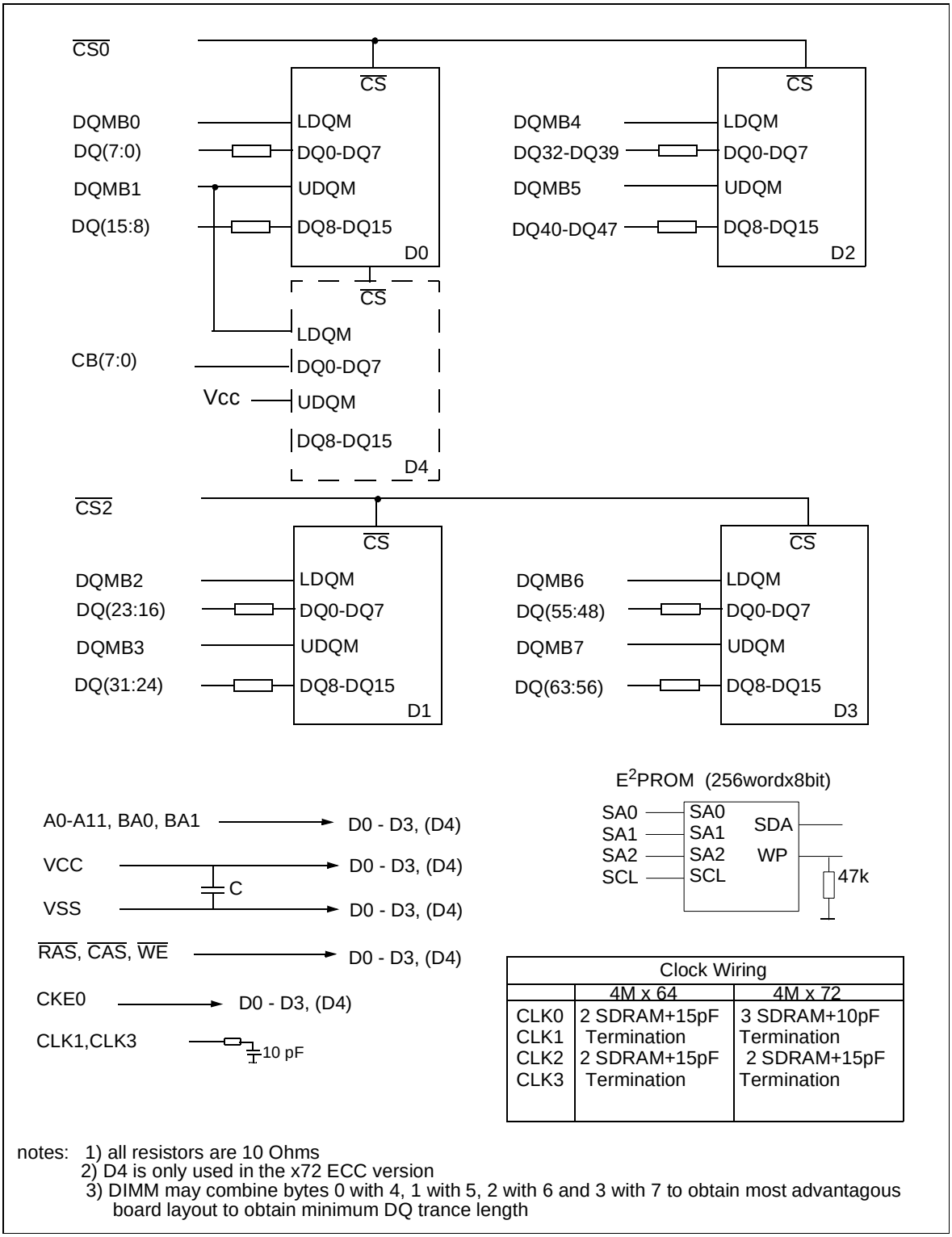
Address Format:

	Part Number	Rows	Columns	Bank Select	Refresh	Period	Interval
4M x 64	HYS64V4200GU	12	8	2	4k	64 ms	15,6 µs
4M x 72	HYS72V4200GU	12	8	2	4k	64 ms	15,6 µs
8M x 64	HYS64V8220GU	12	8	2	4k	64 ms	15,6 µs
8M x 72	HYS72V8220GU	12	8	2	4k	64 ms	15,6 µs

Pin Configuration

PIN #	Symbol	PIN #	Symbol		PIN #	Symbol	PIN #	Symbol
1	VSS	43	VSS		85	VSS	127	VSS
2	DQ0	44	DU		86	DQ32	128	CKE0
3	DQ1	45	CS2		87	DQ33	129	CS3
4	DQ2	46	DQMB2		88	DQ34	130	DQMB6
5	DQ3	47	DQMB3		89	DQ35	131	DQMB7
6	VCC	48	DU		90	VCC	132	NC
7	DQ4	49	VCC		91	DQ36	133	VCC
8	DQ5	50	NC		92	DQ37	134	NC
9	DQ6	51	NC		93	DQ38	135	NC
10	DQ7	52	NC (CB2)		94	DQ39	136	CB6
11	DQ8	53	NC (CB3)		95	DQ40	137	CB7
12	VSS	54	VSS		96	VSS	138	VSS
13	DQ9	55	DQ16		97	DQ41	139	DQ48
14	DQ10	56	DQ17		98	DQ42	140	DQ49
15	DQ11	57	DQ18		99	DQ43	141	DQ50
16	DQ12	58	DQ19		100	DQ44	142	DQ51
17	DQ13	59	VCC		101	DQ45	143	VCC
18	VCC	60	DQ20		102	VCC	144	DQ52
19	DQ14	61	NC		103	DQ46	145	NC
20	DQ15	62	DU		104	DQ47	146	DU
21	NC (CB0)	63	CKE1		105	NC (CB4)	147	NC
22	NC (CB1)	64	VSS		106	NC (CB5)	148	VSS
23	VSS	65	DQ21		107	VSS	149	DQ53
24	NC	66	DQ22		108	NC	150	DQ54
25	NC	67	DQ23		109	NC	151	DQ55
26	VCC	68	VSS		110	VCC	152	VSS
27	WE	69	DQ24		111	CAS	153	DQ56
28	DQMB0	70	DQ25		112	DQMB4	154	DQ57
29	DQMB1	71	DQ26		113	DQMB5	155	DQ58
30	CS0	72	DQ27		114	CS1	156	DQ59
31	DU	73	VCC		115	RAS	157	VCC
32	VSS	74	DQ28		116	VSS	158	DQ60
33	A0	75	DQ29		117	A1	159	DQ61
34	A2	76	DQ30		118	A3	160	DQ62
35	A4	77	DQ31		119	A5	161	DQ63
36	A6	78	VSS		120	A7	162	VSS
37	A8	79	CLK2		121	A9	163	CLK3
38	A10	80	NC		122	BA0	164	NC
39	BA1	81	WP		123	NC	165	SA0
40	VCC	82	SDA		124	VCC	166	SA1
41	VCC	83	SCL		125	CLK1	167	SA2
42	CLK0	84	VCC		126	NC	168	VCC

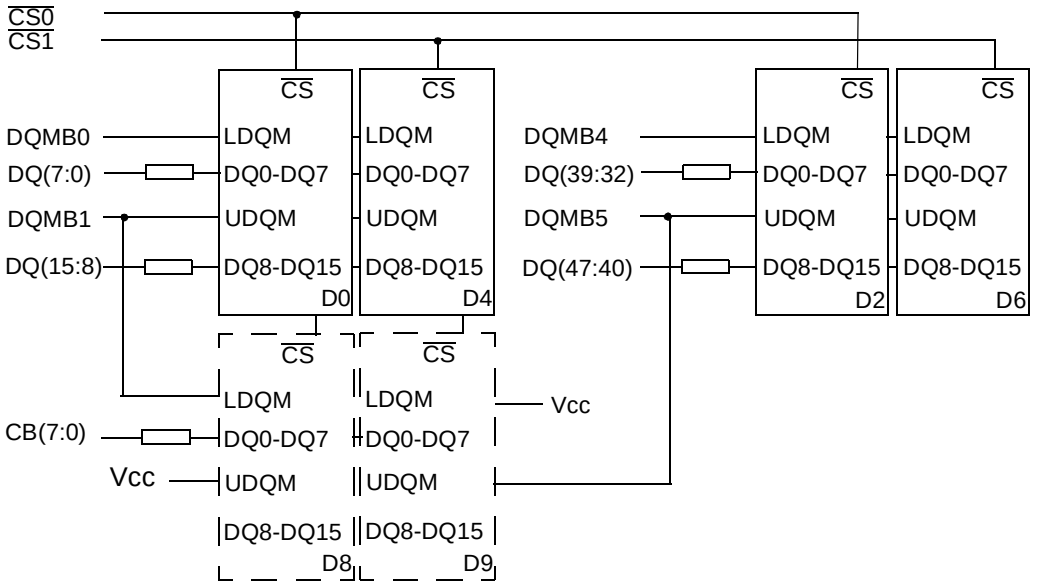
Note : Pinnames in brackets are for the x72 ECC versions

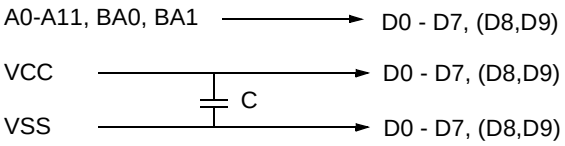


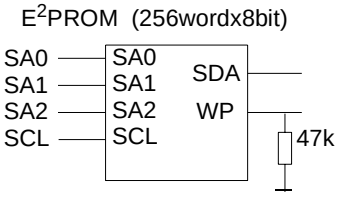
Clock Wiring		
	4M x 64	4M x 72
CLK0	2 SDRAM+15pF	3 SDRAM+10pF
CLK1	Termination	Termination
CLK2	2 SDRAM+15pF	2 SDRAM+15pF
CLK3	Termination	Termination

notes: 1) all resistors are 10 Ohms
2) D4 is only used in the x72 ECC version
3) DIMM may combine bytes 0 with 4, 1 with 5, 2 with 6 and 3 with 7 to obtain most advantagous board layout to obtain minimum DQ trance length

Block Diagram for 4M x 64 and 4M x 72 1 bank SDRAM DIMM modules (HYS64V4200GU)







Clock Wiring		
	8M x 64	8M x 72
CLK0	2 SDRAM+15pF	3 SDRAM+10pF
CLK1	2 SDRAM+15pF	3 SDRAM+10pF
CLK2	2 SDRAM+15pF	2 SDRAM+15pF
CLK3	2 SDRAM+15pF	2 SDRAM+15pF

notes: 1) all resistors are 10 Ohms
2) D8 & D9 are only used in the x72 ECC version
3) DIMM may combine bytes 0 with 4, 1 with 5, 2 with 6 and 3 with 7 to obtain most advantagous board layout to obtain minimum DQ trance length

DC Characteristics

T_A = 0 to 70 °C; V_{SS} = 0 V; V_{DD},V_{DDQ} = 3.3 V ± 0.3 V

Parameter	Symbol	Limit Values		Unit
		min.	max.	
Input high voltage	V_{IH}	2.0	Vcc+ 0.3	V
Input low voltage	V_{IL}	– 0.5	0.8	V
Output high voltage (I_{OUT} = – 2.0 mA)	V_{OH}	2.4	–	V
Output low voltage (I_{OUT} = 2.0 mA)	V_{OL}	–	0.4	V
Input leakage current, any input (0 V < V_{IN} < 3.6 V, all other inputs = 0 V)	$I_{I(L)}$	– 10	10	µA
Output leakage current (DQ is disabled, 0 V < V_{OUT} < V_{CC})	$I_{O(L)}$	– 10	10	µA

Capacitance

T_A = 0 to 70 °C; V_{DD} = 3.3 V ± 0.3 V, f = 1 MHz

Parameter	Symbol	Limit Values		Unit
		max. 4M x 72	max. 8M x 72	
Input capacitance (A0 to A11, $\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$)	C_{I1}	tbd.	tbd.	pF
Input capacitance (CS0 -CS3,)	C_{I2}	tbd.	tbd.	pF
Input capacitance (CLK0 - CLK3)	C_{ICL}	tbd.	tbd.	pF
Input capacitance (CKE0, CKE1)	C_{I3}	tbd.	tbd.	pF
Input capacitance (DQMB0 - DQMB7)	C_{I4}	tbd.	tbd.	pF
Input / Output capacitance (DQ0-DQ63,CB0-CB7)	C_{IO}	tbd.	tbd.	pF
Input Capacitance (SCL,SA0-2)	C_{sc}	8	8	pF
Input/Output Capacitance	C_{sd}	10	10	pF

Operating Currents (T_A = 0 to 70°C, Vdd = 3.3V ± 0.3V 1)

(Recommended Operating Conditions unless otherwise noted)

Parameter & Test Condition		Symb.	-8/-8B	-10		Note
			max.			
OPERATING CURRENT trc=trcmin., tck=tckmin. Ouputs open, Burst Length = 4, CL=3 All banks operated in random access, all banks operated in ping-pong manner to maximize gapless data access		ICC1	130	90	mA	1
PRECHARGE STANDBY CURRENT in Power Down Mode $\overline{CS}$ =VIH (min.), CKE<=Vil(max)	tck = min.	ICC2P	2	2	mA	1
	tck = Infinity	ICC2PS	1	1	mA	1
PRECHARGE STANDBY CURRENT in Non-Power Down Mode $\overline{CS}$ = VIH (min.), CKE>=Vih(min)	tck = min.	ICC2N	35	30	mA	1
	tck = Infinity	ICC2NS	5	5	mA	1
NO OPERATING CURRENT tck = min., $\overline{CS}$ = VIH(min), active state (max. 4 banks)	CKE>=VIH(min.)	ICC3N	45	40	mA	1
	CKE<=VIL(max.)	ICC3P	8	8	mA	1
BURST OPERATING CURRENT tck = min., Read command cycling		ICC4	100	70	mA	1,2
AUTO REFRESH CURRENT tck = min., Auto Refresh command cycling		ICC5	130	90	mA	1
SELF REFRESH CURRENT Self Refresh Mode, CKE=0.2V	standard version	ICC6	1	1	mA	1

AC Characteristics 3)4)

T_A = 0 to 70 °C; V_{SS} = 0 V; V_{CC} = 3.3 V ± 0.3 V, t_T = 1 ns

Parameter	Symbol	Limit Values						Unit	Note
		-8 PC100-222		-8B PC100-323		-10 PC66			
		min.	max.	min.	max.	min.	max.		
Clock and Clock Enable									
Clock Cycle Time	t_{CK}								
$\overline{CAS}$ Latency = 3		10	–	10	–	10	–	ns	
$\overline{CAS}$ Latency = 2		10	–	12	–	15	–	ns	
System Frequency	f_{CK}								
$\overline{CAS}$ Latency = 3		–	100	–	100	–	100	MHz	
$\overline{CAS}$ Latency = 2		–	100	–	83	–	66	MHz	
Clock Access Time	t_{AC}								
$\overline{CAS}$ Latency = 3		–	6	–	6	–	8	ns	4,5)
$\overline{CAS}$ Latency = 2		–	6	–	7	–	9	ns	
Clock High Pulse Width	t_{CH}	3	–	3	–	3.5	–	ns	6)
Clock Low Pulse Width	t_{CL}	3	–	3	–	3.5	–	ns	6)
Input Setup time	t_{CS}	2	–	2	–	3	–	ns	7)
Input Hold Time	t_{CH}	1	–	1	–	1	–	ns	7)
CKE Setup Time (Power down mode)	t_{CKSP}	2.5	–	2.5	–	3	–	ns	8)
CKE Setup Time (Self Refresh Exit)	t_{CKSR}	8	–	10	–	8	–	ns	9)
Transition time (rise and fall)	t_T	1	–	1	–	1	–	ns	
Common Parameters									
$\overline{RAS}$ to $\overline{CAS}$ delay	t_{RCD}	20	–	20	–	30	–	ns	
Precharge Time	t_{RP}	20	–	30	–	30	–	ns	
Active Command Period	t_{RAS}	50	100k	60	100k	70	100k	ns	
Cycle Time	t_{RC}	70	–	80	–	80	–	ns	
Bank to Bank Delay Time	t_{RRD}	16	–	20	–	20	–	ns	
$\overline{CAS}$ to $\overline{CAS}$ delay time (same bank)	t_{CCD}	1	–	1	–	1	–	CLK	

Parameter	Symbol	Limit Values						Unit	Note
		-8 PC100-222		-8B PC100-323		-10 PC66			
		min.	max.	min.	max.	min.	max.		
Refresh Cycle									
Refresh Period (4096 cycles)	t_{REF}	–	64	–	64	–	64	ms	8)
Self Refresh Exit Time	t_{SREX}	10	–	10	–	10	–	ns	9)
Read Cycle									
Data Out Hold Time	t_{OH}	3	–	3		3	–	ns	4)
Data Out to Low Impedance	t_{LZ}	0	–	0		0	–	ns	
Data Out to High Impedance	t_{HZ}	3	8	3	10	3	10	ns	10)
DQM Data Out Disable Latency	t_{DQZ}	–	2	–	2	–	2	CLK	
Write Cycle									
Data input to Precharge (write recovery)	t_{DPL}	2	–	2	–	2	–	CLK	
Data In to Active/refresh	t_{DAL}	5	–	5	–	5	–	CLK	
DQM Write Mask Latency	t_{DQW}	0	–	0	–	0	–	CLK	

Notes:

1. These parameters depend on the cycle rate. These values are measured at 100 MHz for -8 and -8B and at 66 MHz for -10 modules. Input signals are changed once during tck, excepts for ICC6 and for standby currents when tck=infinity. All values are shown per memory component.
2. These parameters are measured with continous data stream during read access and all DQ toggling. CL=3 and BL=4 assumed and the VDDQ current is excluded.
3. All AC characteristics are shown for device level.
   An initial pause of 100µs is required after power-up, then a Precharge All Banks command must be given followed by 8 Auto Refresh (CBR) cycles before the Mode Register Set Operation can begin.
4. AC timing tests have V_{il} = 0.4 V and V_{ih} = 2.4 V with the timing referenced to the 1.4 V crossover point. The transition time is measured between V_{ih} and V_{il}. All AC measurements assume t_T=1ns with the AC output load circuit show. Specified tac and toh parameters are measured with a 50 pF only, without any resistive termination and with a input signal of 1V / ns edge rate between 0.8V and 2.0 V.

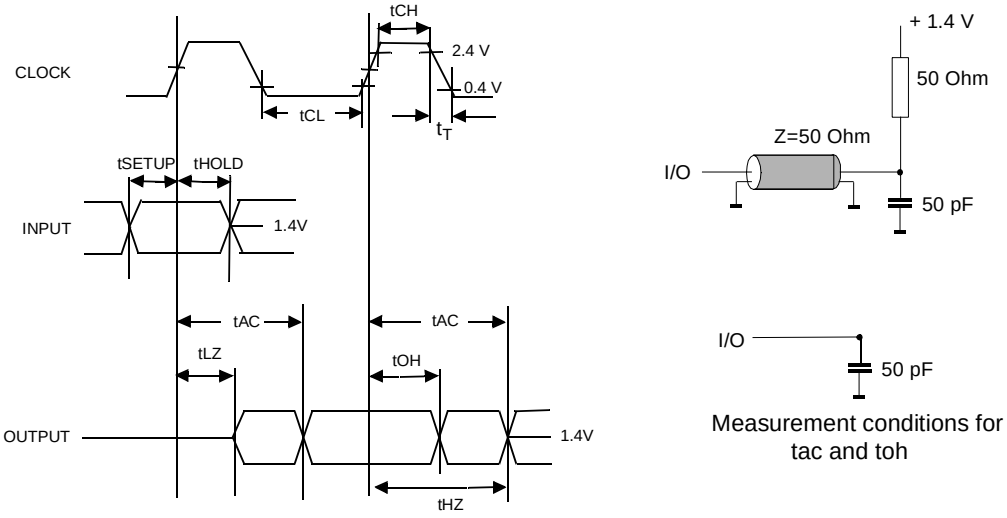


fig.1

5. If clock rising time is longer than 1ns, a time (t_T/2 -0.5) ns has to be added to this parameter.
6. Rated at 1.5 V
7. If t_T is longen than 1 ns, a time (t_T -1) ns has to be added to this parameter.
8. Any time that the refresh Period has been exceeded, a minimum of two Auto (CBR) Refresh commands must be given to “wake-up“ the device.
9. Self Refresh Exit is a synchronous operation and begins on the 2nd positive clock edge after CKE returns high. Self Refresh Exit is not complete until a time period equal to tRC is satisfied once the Self Refresh Exit command is registered.
10. Referenced to the time which the output achieves the open circuit condition, not to output voltage levels.

A serial presence detect storage device - E^2PROM - is assembled onto the module. Information about the module configuration, speed, etc. is written into the E^2PROM device during module production using a serial presence detect protocol (I^2C synchronous 2-wire bus)

SPD-Table for PC100 modules:

Byte#	Description	SPD Entry Value	Hex					
			4Mx64 -8	4Mx64 -8B	4Mx72 -8	8Mx64 -8	8Mx64 -8B	8Mx72 -8
0	Number of SPD bytes	128	80	80	80	80	80	80
1	Total bytes in Serial PD	256	08	08	08	08	08	08
2	Memory Type	SDRAM	04	04	04	04	04	04
3	Number of Row Addresses (without BS bits)	12	0C	0C	0C	0C	0C	0C
4	Number of Column Addresses (for 16 SDRAM)	8	08	08	08	08	08	08
5	Number of DIMM Banks	1 / 2	01	01	01	02	02	02
6	Module Data Width	64	40	40	48	40	40	48
7	Module Data Width (cont'd)	0	00	00	00	00	00	00
8	Module Interface Levels	LVTTL	01	01	01	01	01	01
9	SDRAM Cycle Time at CL=3	10.0 ns	A0	A0	A0	A0	A0	A0
10	SDRAM Access time from Clock at CL=3	6.0 ns	60	60	60	60	60	60
11	Dimm Config (Error Det/Corr.)	none	00	00	02	00	00	02
12	Refresh Rate/Type	Self-Refresh, 15.6µs	80	80	80	80	80	80
13	SDRAM width, Primary	x16	10	10	10	10	10	10
14	Error Checking SDRAM data width	n/a / x8	00	00	08	00	00	08
15	Minimum clock delay for back-to-back random column address	t_{ccd} = 1 CLK	01	01	01	01	01	01
16	Burst Length supported	1, 2, 4, 8 & full page	8F	8F	8F	8F	8F	8F
17	Number of SDRAM banks	4	04	04	04	04	04	04
18	Supported CAS Latencies	CL = 2 & 3	06	06	06	06	06	06
19	CS Latencies	CS latency = 0	01	01	01	01	01	01
20	WE Latencies	WL = 0	01	01	01	01	01	01
21	SDRAM DIMM module attributes	non buffered/ non reg.	00	00	00	00	00	00
22	SDRAM Device Attributes :General	Vcc tol +/- 10%	06	06	06	06	06	06
23	Minimum Clock Cycle Time at CAS Latency = 2	10.0 / 12.0ns	A0	C0	A0	A0	C0	A0
24	Maximum data access time from Clock for CL=2	6.0 / 7.0ns	60	70	60	60	70	60
25	Minimum Clock Cycle Time at CL = 1	not supported	FF	FF	FF	FF	FF	FF
26	Maximum Data Access Time from Clock at CL=1	not supported	FF	FF	FF	FF	FF	FF
27	Minimum Row Precharge Time	20 / 30 ns	14	1E	14	14	1E	14

Byte#	Description	SPD Entry Value	Hex					
			4Mx64 -8	4Mx64 -8B	4Mx72 -8	8Mx64 -8	8Mx64 -8B	8Mx72 -8
28	Minimum Row Active to Row Active delay tRRD	16 ns	10	14	10	10	14	10
29	Minimum RAS to CAS delay tRCD	20 ns	14	14	14	14	14	14
30	Minimum RAS pulse width tRAS	45 ns	2D	2D	2D	2D	2D	2D
31	Module Bank Density (per bank)	32 MByte	08	08	08	08	08	08
32	SDRAM input setup time	2 ns	20	20	20	20	20	20
33	SDRAM input hold time	1 ns	10	10	10	10	10	10
34	SDRAM data input setup time	2 ns	20	20	20	20	20	20
35	SDRAM data input hold time	1 ns	10	10	10	10	10	10
62-61	Superset information (may be used in future)		FF	FF	FF	FF	FF	FF
62	SPD Revision	Revision 1.2	12	12	12	12	12	12
63	Checksum for bytes 0 - 62		D7	15	E9	D8	16	EA
64-125	Manufacturers information (optio-nal) (FFh if not used)		XX	XX	XX	XX	XX	XX
126	Max. Frequency Specification	100 MHz	64	64	64	64	64	64
127	100 Mhz support details		AF	AD	AF	FF	FD	FF
128+	Unused storage locations		FF	FF	FF	FF	FF	FF

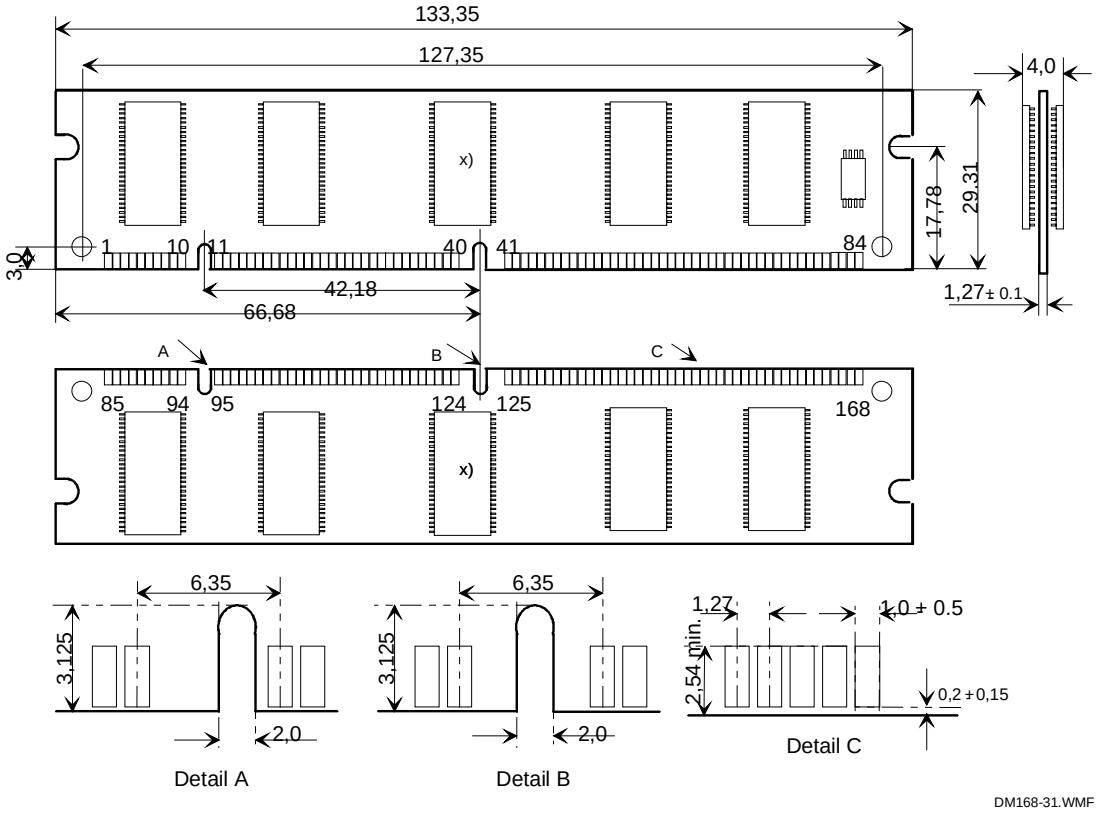
SPD-Table for PC66 modules:

Byte#	Description	SPD Entry Value	Hex			
			4Mx64 -10	4Mx72 -10	8Mx64 -10	8Mx72 -10
0	Number of SPD bytes	128	80	80	80	80
1	Total bytes in Serial PD	256	08	08	08	08
2	Memory Type	SDRAM	04	04	04	04
3	Number of Row Addresses (without BS bits)	12	0C	0C	0C	0C
4	Number of Column Addresses (for x16 SDRAM)	8	08	08	08	08
5	Number of DIMM Banks	1 / 2	01	01	02	02
6	Module Data Width	64	40	48	40	48
7	Module Data Width (cont'd)	0	00	00	00	00
8	Module Interface Levels	LVTTL	01	01	01	01
9	SDRAM Cycle Time at CL=3	10.0 ns	A0	A0	A0	A0
10	SDRAM Access time from Clock at CL=3	7.0 ns	70	70	70	70
11	Dimm Config (Error Det/Corr.)	none	00	02	00	02
12	Refresh Rate/Type	Self-Refresh, 15.6µs	80	80	80	80
13	SDRAM width, Primary	x16	10	10	10	10
14	Error Checking SDRAM data width	n/a / x8	00	08	00	08
15	Minimum clock delay for back-to-back random column address	t_{ccd} = 1 CLK	01	01	01	01
16	Burst Length supported	1, 2, 4, 8 & full page	8F	8F	8F	8F
17	Number of SDRAM banks	4	04	04	04	04
18	Supported CAS Latencies	CL = 2 & 3	06	06	06	06
19	CS Latencies	CS latency = 0	01	01	01	01
20	WE Latencies	WL = 0	01	01	01	01
21	SDRAM DIMM module attributes	non buffered/ non reg.	00	00	00	00
22	SDRAM Device Attributes :General	Vcc tol +/- 10%	06	06	06	06
23	Minimum Clock Cycle Time at CAS Latency = 2	15.0 ns	F0	F0	F0	F0
24	Maximum data access time from Clock for CL=2	8.0 ns	80	80	80	80
25	Minimum Clock Cycle Time at CL = 1	not supported	FF	FF	FF	FF
26	Maximum Data Access Time from Clock at CL=1	not supported	FF	FF	FF	FF
27	Minimum Row Precharge Time	24 ns	18	18	18	18
28	Minimum Row Active to Row Active delay tRRD	20 ns	14	14	14	14

SPD cont'd:

Byte#	Description	SPD Entry Value	Hex			
			4Mx64 -8	4Mx72 -8	8Mx72 -8	8Mx72 -8
29	Minimum RAS to CAS delay tRCD	24 ns	18	18	18	18
30	Minimum RAS pulse width tRAS	60 ns	3C	3C	3C	3C
31	Module Bank Density (per bank)	32 MByte	08	08	08	08
32	SDRAM input setup time	2.5 ns	25	25	25	25
33	SDRAM input hold time	1 ns	10	10	10	10
34	SDRAM data input setup time	2.5 ns	25	25	25	25
35	SDRAM data input hold time	1 ns	10	10	10	10
32-61	Superset information (may be used in future)		FF	FF	FF	FF
62	SPD Revision	Revision 1.2	12	12	12	12
63	Checksum for bytes 0 - 62		7C	8E	7D	8F
64-125	Manufacturers information (optional) (FFh if not used)		XX	XX	XX	XX
126	Max. Frequency Specification	66 MHz	66	66	66	66
127	Support details		AF	AF	FF	FF
128+	Unused storage locations		FF	FF	FF	FF

L-DIM-168-31
SDRAM DIMM Module package



x) on ECC modules only